# ne<mark>x</mark>peria

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Should be replaced with:

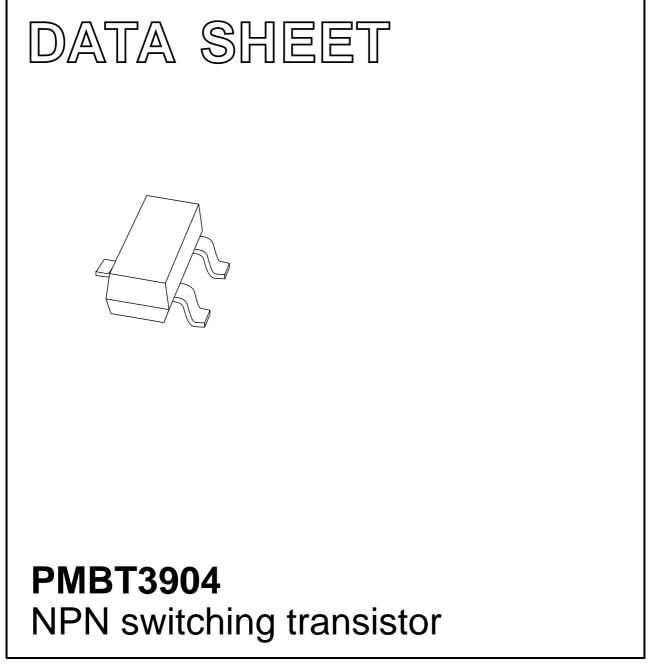
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If you have any questions related to the data sheet, please contact our nearest sales office via e-mail or telephone (details via **salesaddresses@nexperia.com**). Thank you for your cooperation and understanding,

Kind regards,

Team Nexperia

# DISCRETE SEMICONDUCTORS



Product data sheet Supersedes data of 1999 Apr 27 2004 Jan 12



### **PMBT3904**

### FEATURES

- Collector current capability I<sub>C</sub> = 200 mA
- Collector-emitter voltage V<sub>CEO</sub> = 40 V.

### APPLICATIONS

• General switching and amplification.

### DESCRIPTION

NPN switching transistor in a SOT23 plastic package. PNP complement: PMBT3906.

#### MARKING

TYPE NUMBER	MARKING CODE <sup>(1)</sup>
PMBT3904	*1A

#### Note

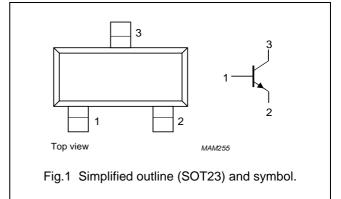
- 1. \* = p: Made in Hong Kong.
  - \* = t : Made in Malaysia.
  - \* = W : Made in China.

### QUICK REFERENCE DATA

SYMBOL	PARAMETER	MAX.	UNIT
V <sub>CEO</sub>	collector-emitter voltage	40	V
I <sub>C</sub>	collector current (DC)	200	mA

#### PINNING

PIN	DESCRIPTION	
1	base	
2	emitter	
3	collector	



### **ORDERING INFORMATION**

TYPE	PACKAGE			
NUMBER	NAME	DESCRIPTION VERSION		
PMBT3904	_	plastic surface mounted package; 3 leads SOT2		

### PMBT3904

### LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V <sub>CBO</sub>	collector-base voltage	open emitter	_	60	V
V <sub>CEO</sub>	collector-emitter voltage	open base	-	40	V
V <sub>EBO</sub>	emitter-base voltage	open collector	-	6	V
I <sub>C</sub>	collector current (DC)		-	200	mA
I <sub>CM</sub>	peak collector current		-	200	mA
I <sub>BM</sub>	peak base current		-	100	mA
P <sub>tot</sub>	total power dissipation	$T_{amb} \le 25 \ ^{\circ}C$ ; note 1	-	250	mW
T <sub>stg</sub>	storage temperature		-65	+150	°C
Tj	junction temperature		-	150	°C
T <sub>amb</sub>	operating ambient temperature		-65	+150	°C

### Note

1. Transistor mounted on an FR4 printed-circuit board.

### THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	note 1	500	K/W

### Note

1. Transistor mounted on an FR4 printed-circuit board.

### CHARACTERISTICS

 $T_{amb}$  = 25 °C unless otherwise specified.

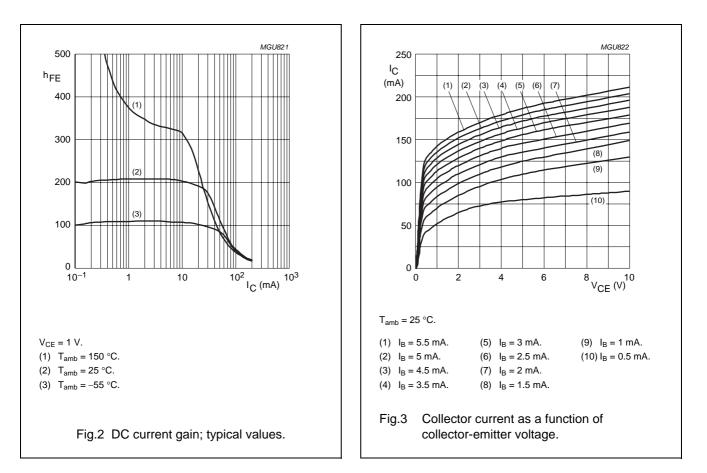
SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
I <sub>CBO</sub>	collector cut-off current	I <sub>E</sub> = 0; V <sub>CB</sub> = 30 V	-	50	nA
I <sub>EBO</sub>	emitter cut-off current	I <sub>C</sub> = 0; V <sub>EB</sub> = 6 V	-	50	nA
h <sub>FE</sub>	DC current gain	V <sub>CE</sub> = 1 V; see Fig.2; note 1			
		I <sub>C</sub> = 0.1 mA	60	-	
		$I_{\rm C} = 1  \rm{mA}$	80	-	
		I <sub>C</sub> = 10 mA	100	300	
		I <sub>C</sub> = 50 mA	60	_	
		I <sub>C</sub> = 100 mA	30	-	
V <sub>CEsat</sub> collector-emitter saturation voltage	$I_{\rm C} = 10 \text{ mA}; I_{\rm B} = 1 \text{ mA}$	-	200	mV	
	voltage	$I_{C} = 50 \text{ mA}; I_{B} = 5 \text{ mA}$	-	300	mV
V <sub>BEsat</sub>	base-emitter saturation voltage	I <sub>C</sub> = 10 mA; I <sub>B</sub> = 1 mA	650	850	mV
		$I_{\rm C} = 50 \text{ mA}; I_{\rm B} = 5 \text{ mA}$	_	950	mV
C <sub>c</sub>	collector capacitance	I <sub>E</sub> = I <sub>e</sub> = 0; V <sub>CB</sub> = 5 V; f = 1 MHz	-	4	pF
C <sub>e</sub>	emitter capacitance	$I_{C} = I_{c} = 0; V_{BE} = 500 \text{ mV};$ f = 1 MHz	-	8	pF

### PMBT3904

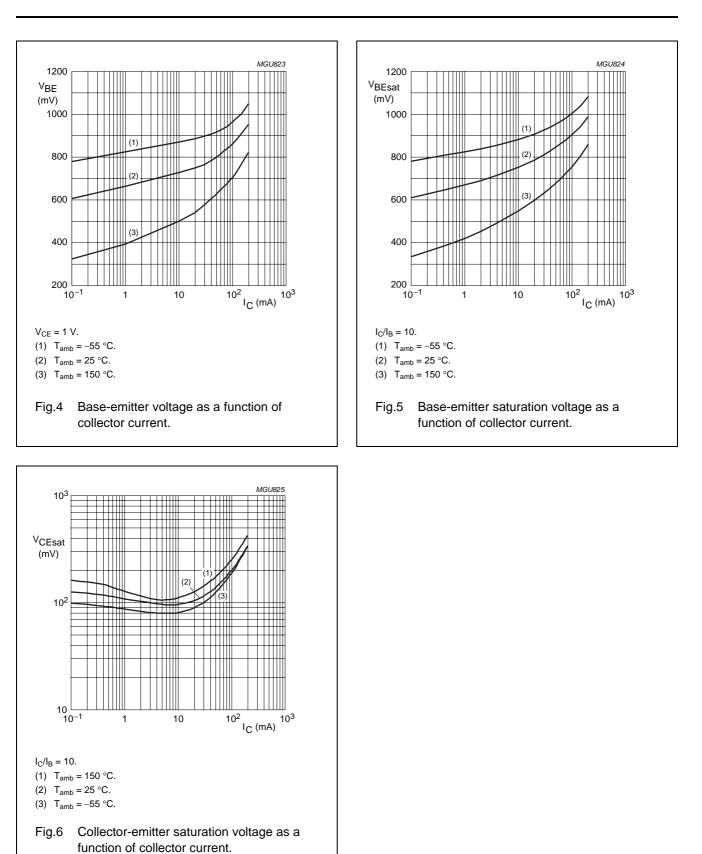
SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
f <sub>T</sub>	transition frequency	I <sub>C</sub> = 10 mA; V <sub>CE</sub> = 20 V; f = 100 MHz	300	-	MHz
F	noise figure	$I_{C}$ = 100 μA; V <sub>CE</sub> = 5 V; R <sub>S</sub> = 1 kΩ; f = 10 Hz to 15.7 kHz	-	5	dB
Switching ti	mes (between 10% and 90% lev	els); see Fig.3			
t <sub>d</sub>	delay time	I <sub>Con</sub> = 10 mA; I <sub>Bon</sub> = 1 mA;	_	35	ns
t <sub>r</sub>	rise time	$I_{Boff} = -1 \text{ mA}$	-	35	ns
ts	storage time		-	200	ns
t <sub>f</sub>	fall time		-	50	ns

#### Note

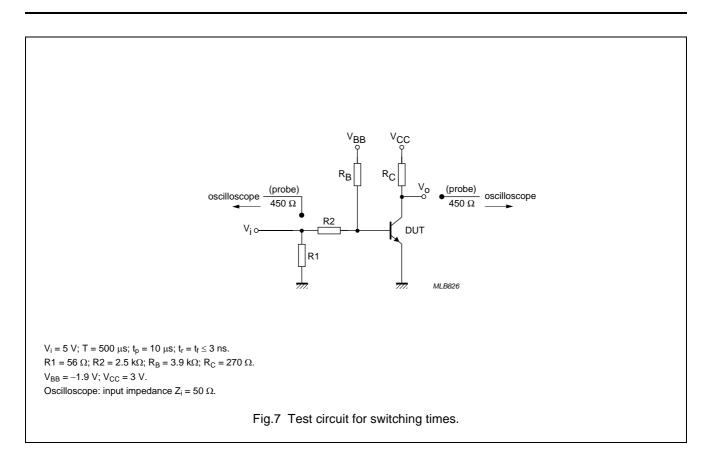
1. Pulse test:  $t_p \leq 300~\mu s;~\delta \leq 0.02.$ 



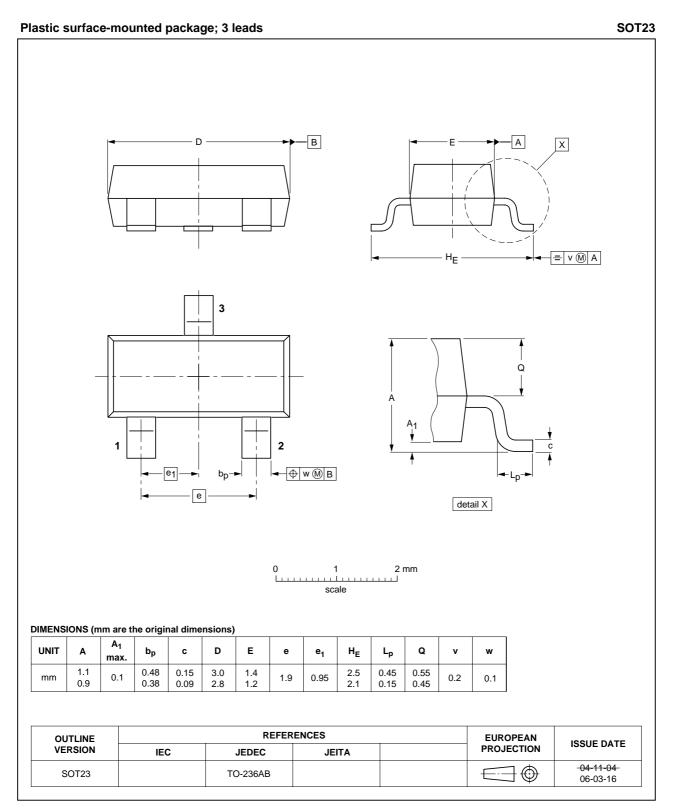
## PMBT3904



### PMBT3904



### PACKAGE OUTLINE



PMBT3904

PMBT3904

### DATA SHEET STATUS

DOCUMENT STATUS <sup>(1)</sup>	PRODUCT STATUS <sup>(2)</sup>	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

#### Notes

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# **NXP Semiconductors**

### **Customer notification**

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#### **Contact information**

For additional information please visit: http://www.nxp.com For sales offices addresses send e-mail to: salesaddresses@nxp.com

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